PATENT APPLICATION

		IN THE UNITED STATES PATE	NT AND TRADEMARK OFFICE	4				
In re	the Ap	oplication of:						
TAM	ATSU	KA		•				
Seria	al No.:	New Application	Group Art Unit:					
Filed	l: July	9, 2001	Examiner:					
For:	For: SILICON SINGLE CRYSTAL WAFER AND MANUFACTURING PROCESS THEREFOR							
		INFORMATION DISCL	OSURE STATEMENT					
		ner for Patents , D.C. 20231	July 9, 2001					
Sir:								
item(prose	nation i s) is att ecution	item(s) listed on the attached PTO-1449. Lached. It is respectfully requested that the	Patent and Trademark Office is hereby directed Inless otherwise indicated herein, one copy of information be expressly considered during the made of record therein and appear among the	each				
	1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date or the date of filing a CPA, OR (b) before the mailing date of a first Office Action on the merits in the present application, or (c) accompanies a Request for Continued Examination. No certification or fee is required.							
	2. This Information Disclosure Statement is being filed more than three months after the U.S. filing date AND after the mailing date of the first Office Action on the merits, but before the mailing date of a Final Rejection or Notice of Allowance.							
		Statement was cited in a communication from	ormation contained in this Information Disclosure om a foreign patent office in a counterpart foreign or to the filing of this Information Disclosure State	1				
		cited in a communication from a foreign pat knowledge after making reasonable inquiry	nation in this Information Disclosure Statement went office in a counterpart foreign application or, was known to any individual designated in 37 Ce filing of this Information Disclosure Statement.	to my				
			payment of the fee under 37 CFR §1.17(p). Ple rpayment to Deposit Account No. 01-2300 as nec					

09/868901 Application No. JC18 Rec'd FST/PTO 0 9 JUL 2001

	3. This Information Disclosure Statement is being filed more than three months after the U.S date and after the mailing date of a Final Rejection or Notice of Allowance, but before payment of Issue Fee. Applicant(s) hereby petition(s) that the Information Disclosure Statement be considered Attached is our check in the amount of \$180.00 in payment of the petition fee under 37 CFR §1.1 Please charge any fee deficiency or credit any overpayment to Deposit Account No. 01-2300 as reto ensure consideration of the disclosed information.				
		a. I hereby certify that each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement. 37 CFR §1.97(e)(1).			
		b. I hereby certify that no item of information in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to my knowledge after making reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this Information Disclosure Statement. 37 CFR §1.97(e)(2).			
\boxtimes	4. of the	The reference(s) was/were cited in a counterpart foreign application. An English language version International Search Report is attached for the Examiner's information.			
\boxtimes	5.	In the event any fees are due with this paper, please charge our Deposit Account No. 01-2300.			
		Respectfully submitted,			

David T. Nikaido Registration No. 22,663

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Tel: (202) 857-6000 Fax: (202) 638-4810

DTN/hk International Search Report 2 References

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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.	SERIAL NO.
P107242-00019	New Application
APPLICANT	
TAMATSUKA	
FILING DATE	GROUP

July 9, 2001

LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

				ENT DOCUMENTS			
EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						

FOREIGN PATENT DOCUMENTS

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	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	TR/ YES	ANSLAT	<u>FION</u> PART.
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

АМ	Abstract of Japanese Patent Publication No. 11195565A; dated July 21, 1999
AN	"Dynamic Behavior of Intrinsic Point Defects in FZ and CZ Silicon Crystals," Mat. Res. Soc. Symp. Proc. Vol. 262, 1992 Materials Research Society, ABE et al., pp. 3-13
AO	

EXAMINER		DATE CONSIDERED
*EXAMINER:	Initial if reference considered, whether or not citation is in conformance and not considered. Include copy of this fo	n conformance with MPEP 609; Draw line through citation if not in